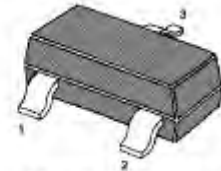
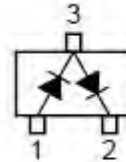


## BAV99 SWITCHING DIODES

### FEATURES

Fast Switching Speed  
For General Purpose Switching Applications  
High Conductance



Marking Code: A7  
SOT-23 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	85	V
Continuous Reverse Voltage	$V_R$	75	V
Continuous Forward Current (Double Diode Loaded)	$I_F$	125	mA
Continuous Forward Current (Single Diode Loaded)	$I_F$	215	mA
Repetitive Peak Forward Current	$I_{FRM}$	450	mA
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	at $t = 1\text{ s}$ 0.5	A
		at $t = 1\text{ ms}$ 1	
		at $t = 1\text{ }\mu\text{s}$ 4.5	
Power Dissipation	$P_{tot}$	350	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit			
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	$V_F$	0.715 0.855 1 1.25	V			
Reverse Current at $V_R = 25\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 25\text{ V}, T_j = 150\text{ }^\circ\text{C}$ at $V_R = 75\text{ V}, T_j = 150\text{ }^\circ\text{C}$		$I_R$		30 1 30 50	nA $\mu\text{A}$ $\mu\text{A}$ $\mu\text{A}$	
Diode Capacitance at $V_R = 0, f = 1\text{ MHz}$				$C_d$	1.5	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}, I_R = 1\text{ mA}, R_L = 100\text{ }\Omega$				$t_{rr}$	4	ns

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## Typical Characteristics

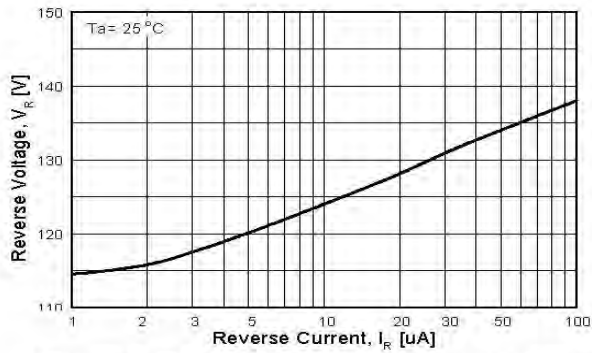


Figure 1. Reverse Voltage vs Reverse Current  
BV - 1.0 to 100uA

## BAV99

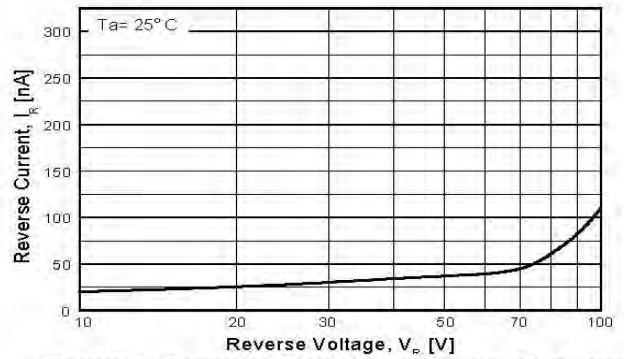


Figure 2. Reverse Current vs Reverse Voltage  
IR - 10 to 100 V

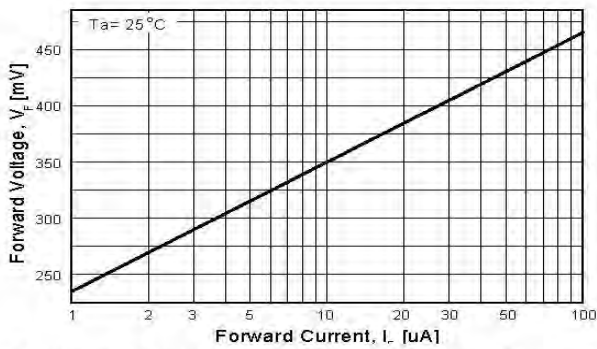


Figure 3. Forward Voltage vs Forward Current  
VF - 1.0 to 100 uA

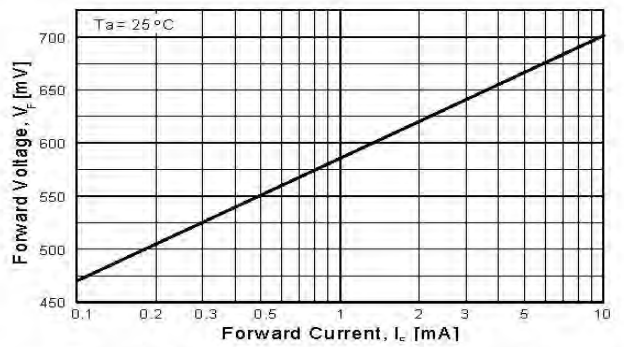


Figure 4. Forward Voltage vs Forward Current  
VF - 0.1 to 10 mA

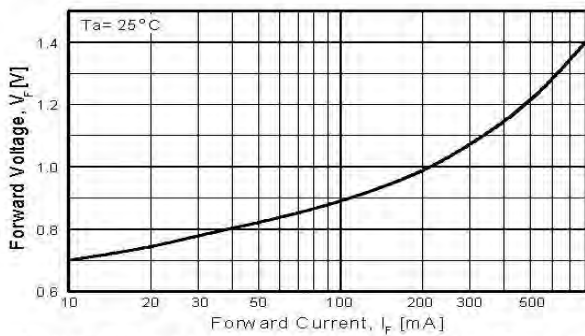


Figure 5. Forward Voltage vs Forward Current  
VF - 10 - 800 mA

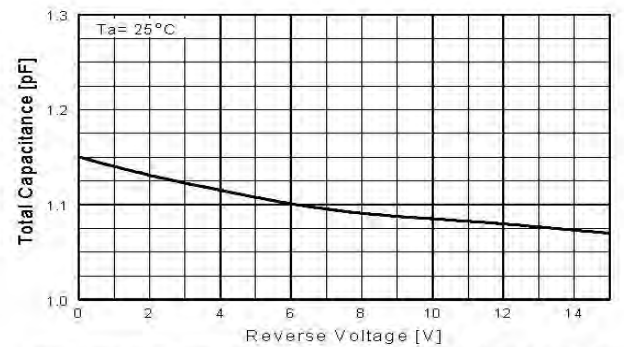


Figure 6. Total Capacitance vs Reverse Voltage

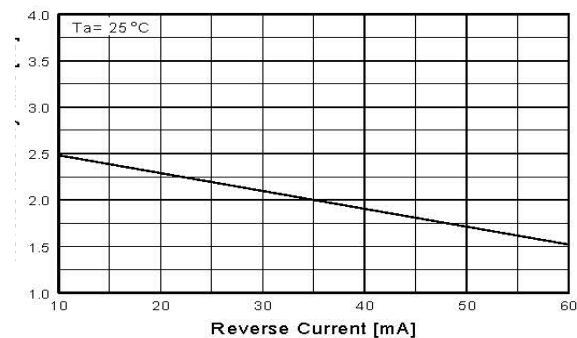


Figure 7. Reverse Recovery Time  
vs Reverse Current  
TRR - IR 10 mA vs 60 mA

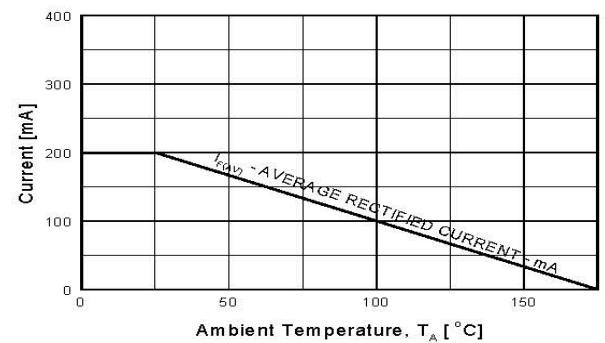
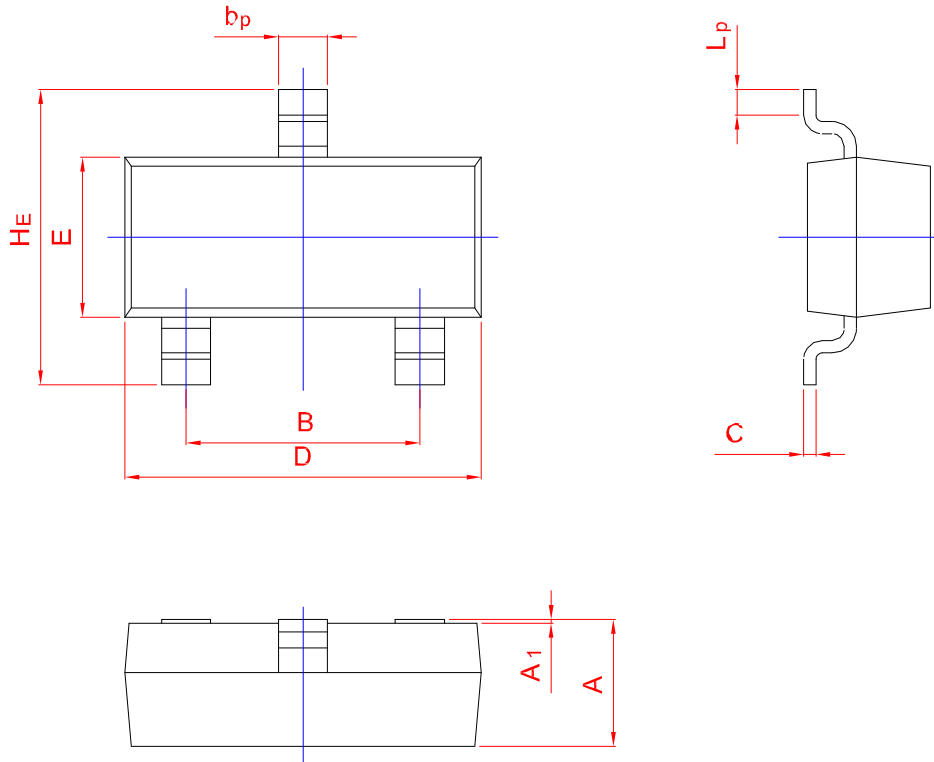
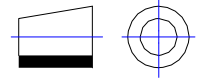


Figure 8. Average Rectified Current ( $I_{F(AV)}$ )  
versus Ambient Temperature ( $T_A$ )

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b <sub>p</sub>	C	D	E	H <sub>E</sub>	A <sub>1</sub>	L <sub>p</sub>
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20

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